

PNP Epitaxial Planar High Current (High Performance) Transistor

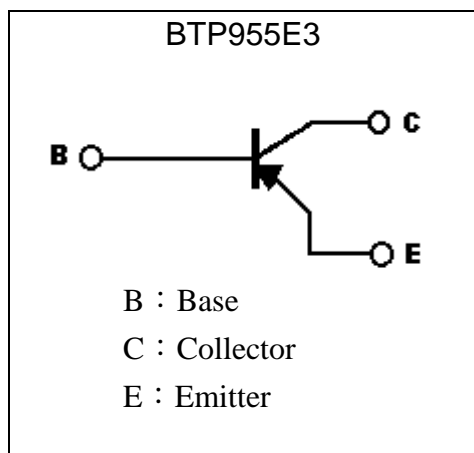
BTP955E3

BV_{CEO}	-140V
I_C	-5A
$R_{CE(SAT)}$	90mΩ typ.

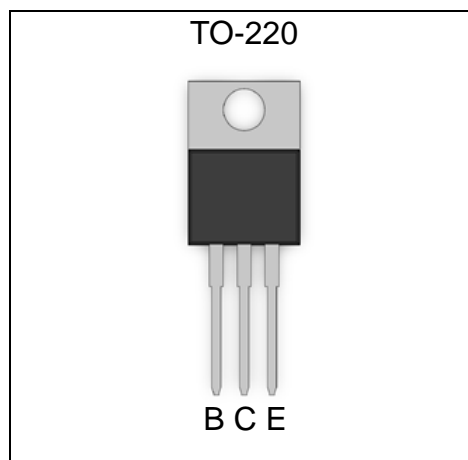
Features

- 5 Amps continuous current, up to 10 Amps peak current
- Very low saturation voltage
- Excellent gain characteristics specified up to 3 Amps
- Extremely low equivalent on resistance, $R_{CE(SAT)}=90m\Omega$ at 3A
- RoHS compliant package

Symbol

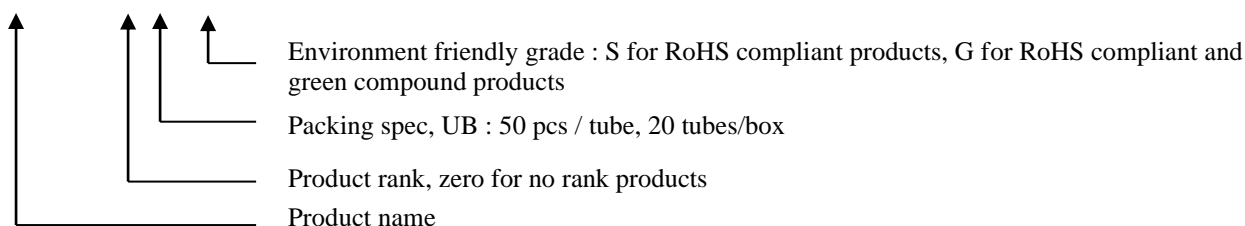


Outline



Ordering Information

Device	Package	Shipping
BTP955E3-0-UB-G	TO-220 (Pb-free lead plating)	50 pcs / tube , 20 tubes / box , 5 boxes/carton





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	-180	V
Collector-Emitter Voltage	V _{CEO}	-140	
Emitter-Base Voltage	V _{EBO}	-6	
Continuous Collector Current	I _C	-5	A
Peak Collector Current	I _{CP}	-10 (Note 1)	
Base Current	I _B	-1	
Power Dissipation @T _A =25°C	P _D	2	W
Power Dissipation @T _C =25°C		31	
Operating and Storage Temperature Range	T _j ; T _{stg}	-55 ~ +150	°C

Note: 1.Single pulse, Pw≤10ms

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient	R _{θJA}	62.5	°C/W
Thermal Resistance, Junction to Case	R _{θJC}	4	

Characteristics (Ta=25°C, unless otherwise specified)

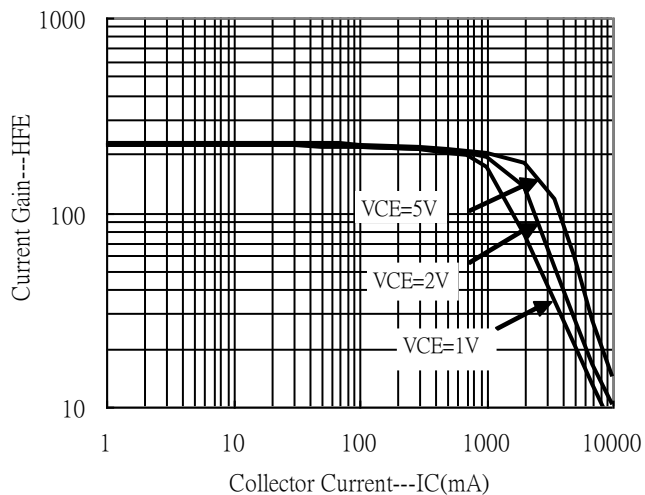
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	-180	-210	-	V	I _C =-100μA
*BV _{CEO}	-140	-170	-		I _C =-10mA
BV _{EBO}	-6	-8	-		I _E =-100μA
I _{CB0}	-	-	-50	nA	V _{CB} =-150V
I _{EBO}	-	-	-10		V _{EB} =-6V
*V _{CE(sat)1}	-	-40	-60	mV	I _C =-100mA, I _B =-5mA
*V _{CE(sat)2}	-	-70	-120		I _C =-500mA, I _B =-50mA
*V _{CE(sat)3}	-	-110	-170		I _C =-1A, I _B =-100mA
*V _{CE(sat)4}	-	-270	-370		I _C =-3A, I _B =-300mA
*V _{BE(sat)}	-	-930	-1110		I _C =-3A, I _B =-300mA
*V _{BE(on)}	-	-830	-950		V _{CE} =-5V, I _C =-3A
R _{CE(sat)}	-	90	123		mΩ
h _{FE1}	100	200	-	-	V _{CE} =-5V, I _C =-10mA
*h _{FE2}	150	200	400	-	V _{CE} =-5V, I _C =-1A
*h _{FE3}	75	140	-	-	V _{CE} =-5V, I _C =-3A
*h _{FE4}	-	10	-	-	V _{CE} =-5V, I _C =-10A
f _T	-	110	-	MHz	V _{CE} =-10V, I _C =-100mA, f=50MHz
Cob	-	40	-	pF	V _{CB} =-20V, f=1MHz

*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

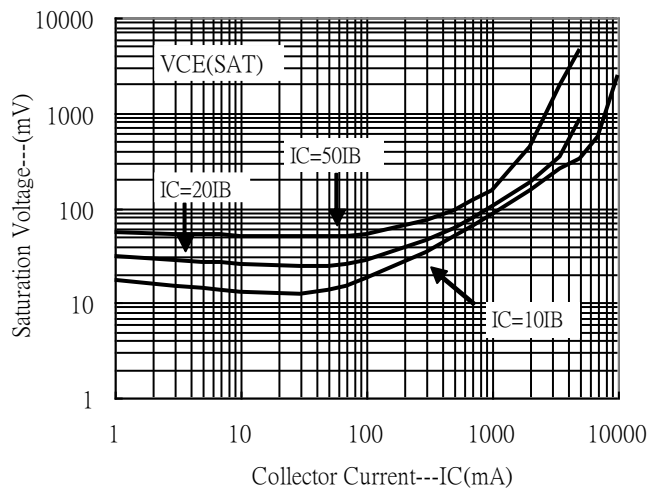


Typical Characteristics

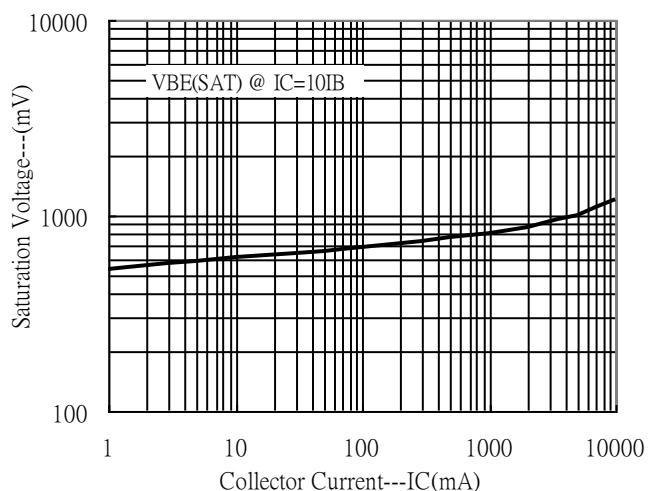
Current Gain vs Collector Current



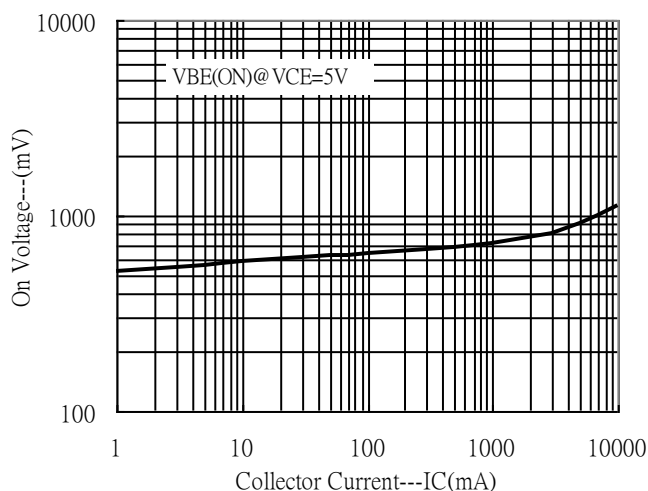
Saturation Voltage vs Collector Current



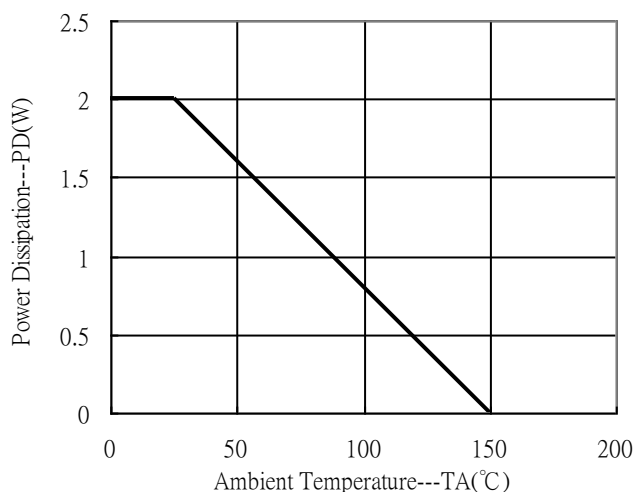
Saturation Voltage vs Collector Current



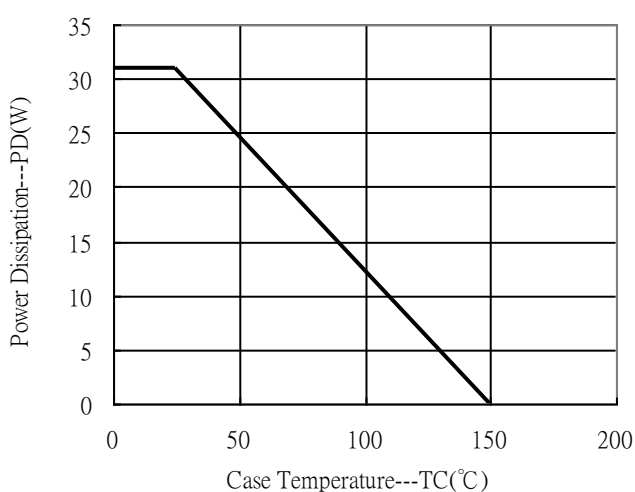
On Voltage vs Collector Current



Power Derating Curve



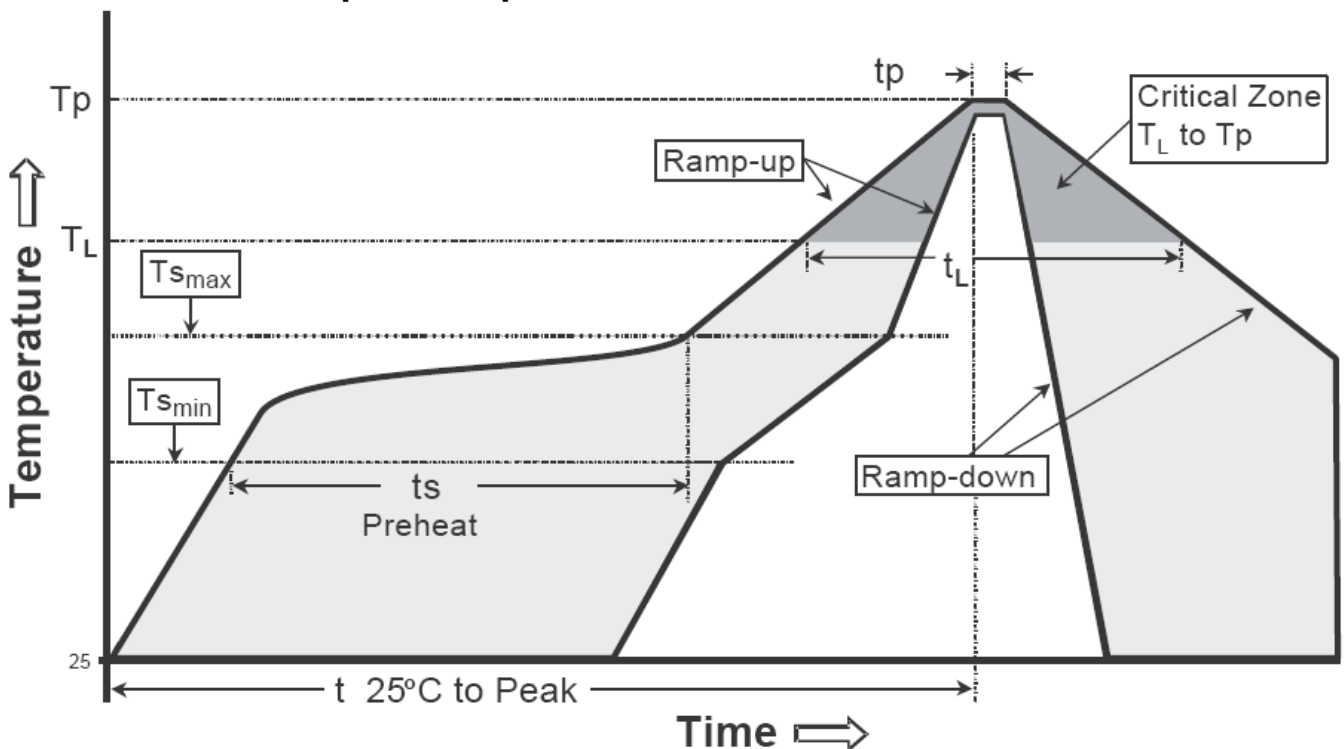
Power Derating Curve



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

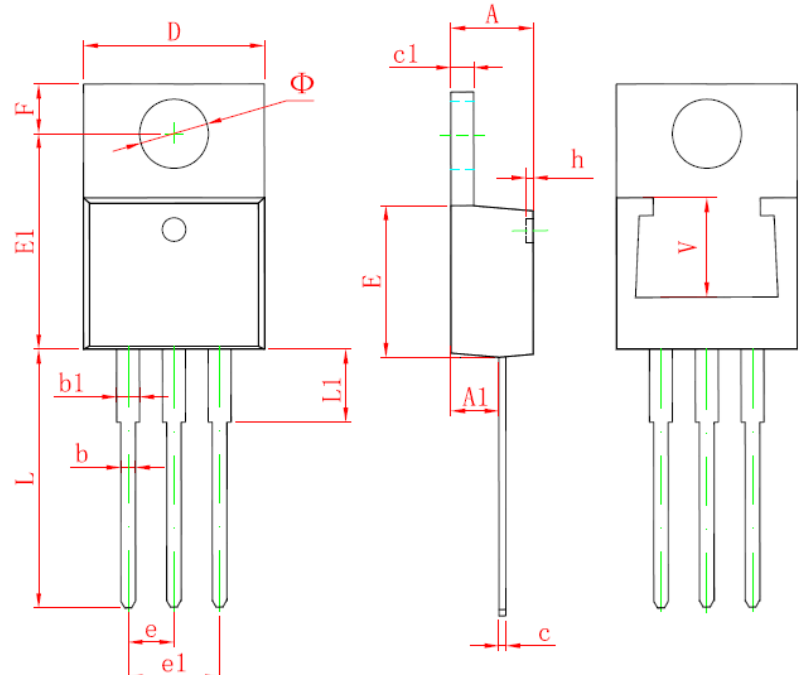
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

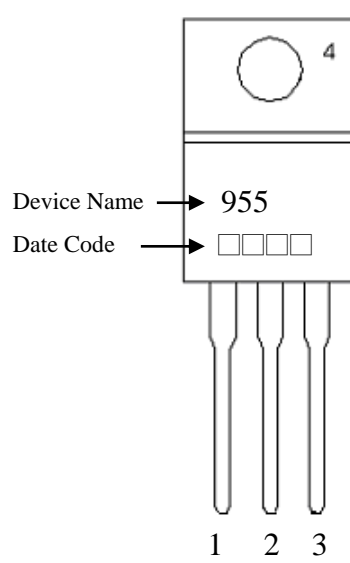
Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-220 Dimension



3-Lead TO-220 Plastic Package
 CYStek Package Code: E3

Marking:



Device Name → 955
 Date Code → □□□□

Style: Pin 1.Base 2.Collector 3.Emitter
 4.Collector

Date Code(counting from left to right) :
 1st code: year code, the last digit of Christian year
 2nd code : month code, Jan→A, Feb→B, Mar→C,
 Apr→D, May→E, Jun→F, Jul→G, Aug→H,
 Sep→J, Oct→K, Nov→L, Dec→M
 3rd and 4th codes : production serial number, 01~99

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184	e	2.540 TYP.		0.100 TYP.	
A1	2.520	2.820	0.099	0.111	e1	4.980	5.180	0.196	0.204
b	0.710	0.910	0.028	0.036	F	2.590	2.890	0.102	0.114
b1	1.170	1.370	0.046	0.054	h	0.000	0.300	0.000	0.012
c	0.310	0.530	0.012	0.021	L	13.400	13.800	0.528	0.543
c1	1.170	1.370	0.046	0.054	L1	3.560	3.960	0.140	0.156
D	10.010	10.310	0.394	0.406	Φ	3.735	3.935	0.147	0.155
E	8.500	8.900	0.335	0.350	V	5.600 REF.		0.220 REF.	
E1	12.060	12.460	0.475	0.491					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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